EGISMOS

IR Laser Diode

Application Industrial use / Biomedical Property

Wavelength $\lambda = 808$ nm Output Power = 500mW Package Type = φ 5.6mm

Egismos currently markets AlGaAs infrared laser diodes in the 780nm ~ 1550nm wavelengths range. The low operating current and high temperature of the laser diodes are achieved through using misoriented substrate and MQW (Strain compensated) active layer. Egismos laser diodes are highly rated in a broad range of applications including, but not limited to, laser pointers, green lasers, blue laser DVD, laser barcode scanners, diode laser equipments, medical instruments and aerospace applications.



IR Laser Diode Key features

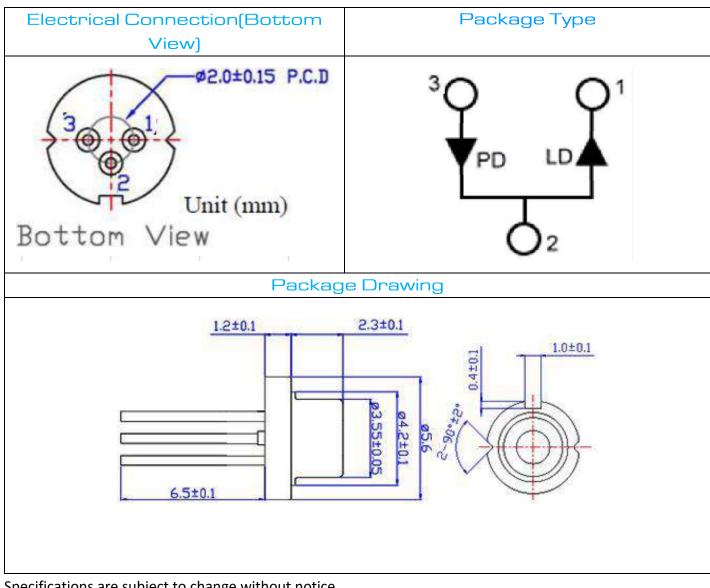
Absolute Maximum Rating at Tc=25°C							
Items	Symbols	Values	Unit				
Optical Output Power	Po(CW)	500	mW				
Reverse Voltage	V	2	V				
Operating Temperature	То	-10~+40	°C				
Storage Temperature	Ts	-10~+70	°C				

Electrical and Optical Characteristics at Tc=25 \degree							
Item	Symbols	Min	Тур.	Max.	Unit	Condition	
Optical Output Power	Ро	-	-	500	mW	-	
Threshold Current	lth	-	50	70	mA	-	
Operating Current	Іор	-	650	700	mA	Po=500mW	
Operating Voltage	Vop		1.8	2.1	V	Po=500mW	
Peak Wavelength	λр	805	808	811	nm	Po=500mW	





	808nm Laser Diode			<u>D6-4-808-500</u>		
Beam Divergence	θ//	9	12	15	deg	Po=500mW
	θ	28	30	35	deg	Po=500mW



Specifications are subject to change without notice.



